MC74HCT20A

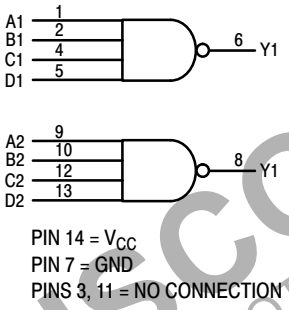
Dual 4-Input NAND Gate with LSTTL-Compatible Inputs

High−Performance Silicon−Gate CMOS

The MC74HCT20A is identical in pinout to the LS20. The device inputs are compatible with standard CMOS LSTTL outputs.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 V to 5.5 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- These are Pb−Free Devices



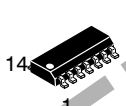
$Y = \overline{ABCD}$

Figure 1. Logic Diagram

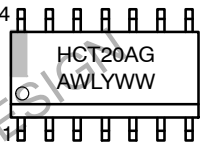
ON Semiconductor®

http://onsemi.com

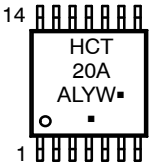
MARKING DIAGRAMS



SOIC−14
D SUFFIX
CASE 751A



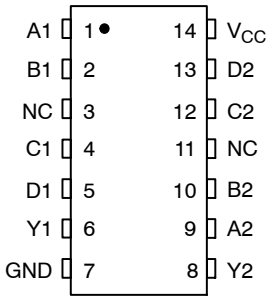
TSSOP−14
DT SUFFIX
CASE 948G



A	= Assembly Location
WL, L	= Wafer Lot
YY, Y	= Year
WW, W	= Work Week
G or ▪	= Pb−Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



FUNCTION TABLE

Inputs				Output
A	**B**	**C**	**D**	**Y**
L	X	X	X	H
X	L	X	X	H
X	X	L	X	H
X	X	X	L	H
H	H	H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	−0.5 to +7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	−0.5 to V_{CC} +0.5	V
V_{out}	DC Output Voltage (Referenced to GND)	−0.5 to V_{CC} +0.5	V
I_{in}	DC Input Current, per Pin	±20	mA
I_{out}	DC Output Current, per Pin	±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	±50	mA
P_D	Power Dissipation in Still Air SOIC Package TSSOP Package	500 450	mW
T_{stg}	Storage Temperature	−65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature Range, All Package Types	− 55	+ 125	°C
t_r, t_f	Input Rise/Fall Time (Figure 1)	0	500	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V_{CC} V	Guaranteed Limit −55 to 25°C	Guaranteed Limit ≤85°C	Guaranteed Limit ≤125°C	Unit
V_{IH}	Minimum High−Level Input Voltage	V_{out} = 0.1V $\|I_{out}\|$ ≤ 20μA	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V_{IL}	Maximum Low−Level Input Voltage	V_{out} = V_{CC} − 0.1V $\|I_{out}\|$ ≤ 20μA	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V_{OH}	Minimum High−Level Output Voltage	V_{in} = V_{IL} $\|I_{out}\|$ ≤ 20μA	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		V_{in} = V_{IL} $\|I_{out}\|$ ≤ 4.0mA	4.5	3.98	3.84	3.70	
V_{OL}	Maximum Low−Level Output Voltage	V_{in} = V_{IH} $\|I_{out}\|$ ≤ 20μA	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		V_{in} = V_{IH} $\|I_{out}\|$ ≤ 4.0mA	4.5	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	V_{in} = V_{CC} or GND	5.5	±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	V_{in} = V_{CC} or GND I_{out} = 0μA	5.5	1	10	40	μA

Symbol	Parameter	Condition	V_{CC} V	≥ −55°C	25 to 125°C	Unit
ΔI_{CC}	Additional Quiescent Supply Current	V_{in} = 2.4V, Any One Input V_{in} = V_{CC} or GND, Other Inputs I_{out} = 0μA	5.5	2.9	2.4	mA

1. Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High−Speed CMOS Data Book (DL129/D).
2. Total Supply Current = I_{CC} + $\Sigma\Delta I_{CC}$.

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input $t_r = t_f$ = 6 ns, V_{CC} = 5.0 V)

Symbol	Parameter	Guaranteed Limit			Unit
		– 55 to 25°C	≤ 85°C	≤ 125°C	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A, B, or C to Output Y (Figures 2 and 3)	28	35	42	ns
t_{TLH}, t_{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 3)	15	19	22	ns
C_{in}	Maximum Input Capacitance	10	10	10	pF

		Typical @ 25°C, V_{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Gate)	26	pF

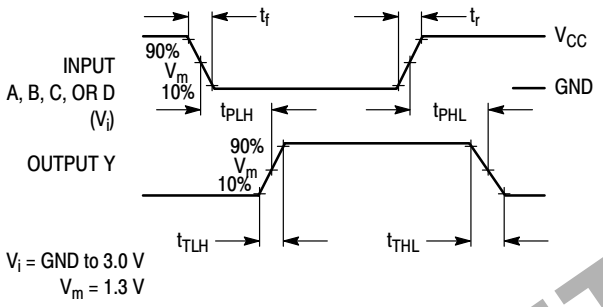
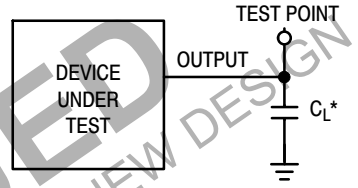


Figure 2. Switching Waveforms



*Includes all probe and jig capacitance

Figure 3. Test Circuit

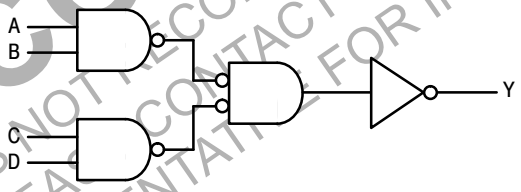
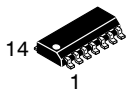


Figure 4. Expanded Logic Diagram (1/2 of the Device)

ORDERING INFORMATION

Device	Package	Shipping†
MC74HCT20ADG	SOIC–14 (Pb–Free)	55 Units/Rail
MC74HCT20ADR2G	SOIC–14 (Pb–Free)	2500/Tape & Reel
MC74HCT20ADTR2G	TSSOP–14*	

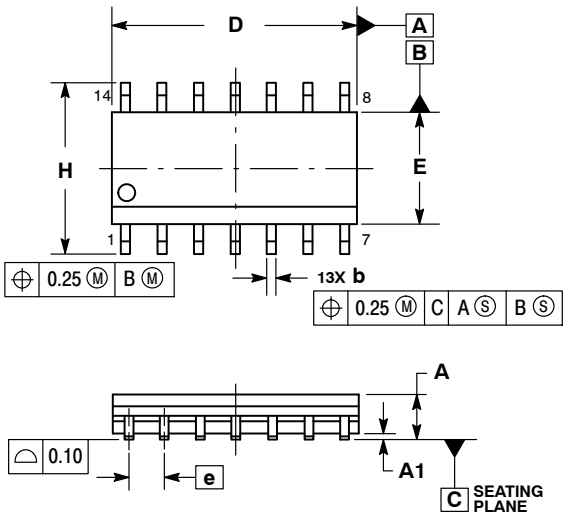
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb–Free.

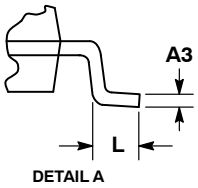


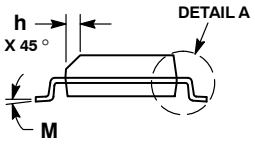
SCALE 1:1

SOIC−14 NB
CASE 751A−03
ISSUE L

DATE 03 FEB 2016



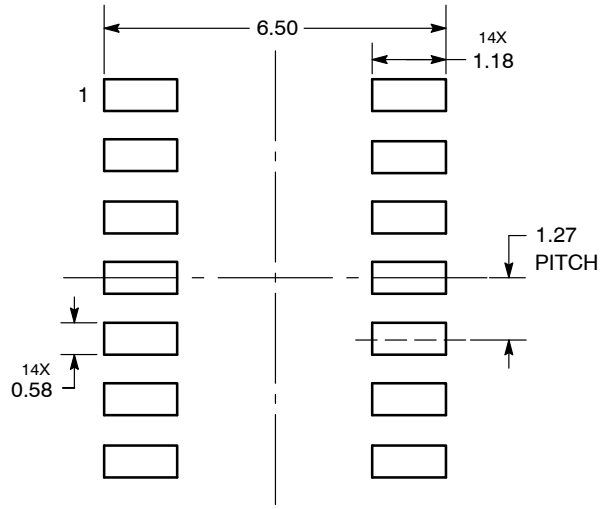




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7 °	0 °	7 °

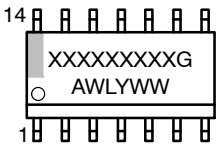
SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42565B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOIC−14 NB**		**PAGE 1 OF 2**

SOIC−14
CASE 751A−03
ISSUE L

DATE 03 FEB 2016

STYLE 1:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. NO CONNECTION
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. NO CONNECTION
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 2:
CANCELLED

STYLE 3:
PIN 1. NO CONNECTION
2. ANODE
3. ANODE
4. NO CONNECTION
5. ANODE
6. NO CONNECTION
7. ANODE
8. ANODE
9. ANODE
10. NO CONNECTION
11. ANODE
12. ANODE
13. NO CONNECTION
14. COMMON CATHODE

STYLE 4:
PIN 1. NO CONNECTION
2. CATHODE
3. CATHODE
4. NO CONNECTION
5. CATHODE
6. NO CONNECTION
7. CATHODE
8. CATHODE
9. CATHODE
10. NO CONNECTION
11. CATHODE
12. CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 5:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. NO CONNECTION
7. COMMON ANODE
8. COMMON CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. ANODE/CATHODE
12. ANODE/CATHODE
13. NO CONNECTION
14. COMMON ANODE

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. ANODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE

STYLE 7:
PIN 1. ANODE/CATHODE
2. COMMON ANODE
3. COMMON CATHODE
4. ANODE/CATHODE
5. ANODE/CATHODE
6. ANODE/CATHODE
7. ANODE/CATHODE
8. ANODE/CATHODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. COMMON CATHODE
12. COMMON ANODE
13. ANODE/CATHODE
14. ANODE/CATHODE

STYLE 8:
PIN 1. COMMON CATHODE
2. ANODE/CATHODE
3. ANODE/CATHODE
4. NO CONNECTION
5. ANODE/CATHODE
6. ANODE/CATHODE
7. COMMON ANODE
8. COMMON ANODE
9. ANODE/CATHODE
10. ANODE/CATHODE
11. NO CONNECTION
12. ANODE/CATHODE
13. ANODE/CATHODE
14. COMMON CATHODE

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales